

Poster Presentation

[AMDp1]Oxide TFTs

Thu. Nov 28, 2019 10:40 AM - 1:10 PM Main Hall (1F)

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[AMDp1-11]Investigation of Hump Phenomenon in a-IGZO Thin-Film Transistors under Positive Bias Stress

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Keywords:a-IGZO TFT, positive bias stress, hump phenomenon, parasitic channel

The hump phenomenon in InGaZnO thin-film transistors (IGZO TFTs) under positive bias stress (PBS) has been investigated by varying channel width and extended length. The results show that the parasitic channel is located at the edge area of the active region along the spreading current direction.